

Silicon PNP Power Transistors

2N6467 2N6468

DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Complement to type 2N6465 2N6466

APPLICATIONS

- For use in audio amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

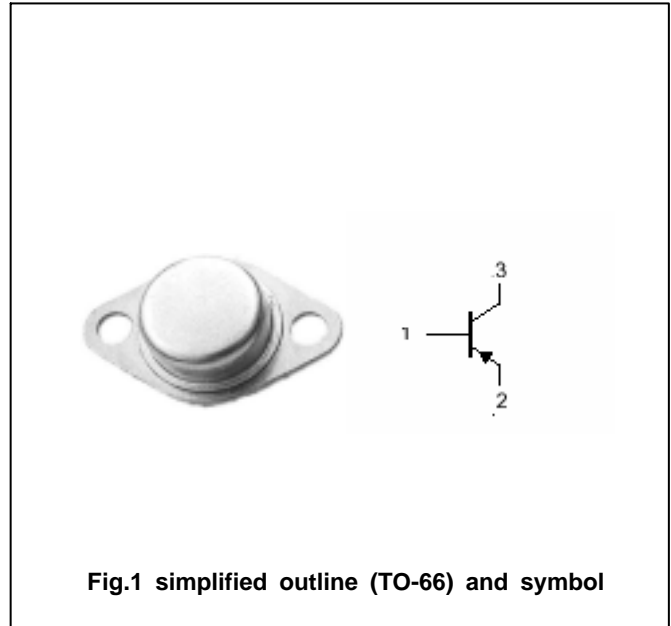


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6467	-110	V
		2N6468	-130	
V _{CEO}	Collector-emitter voltage	2N6467	-100	V
		2N6468	-120	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
P _D	Total power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	2.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6467	-100			V
		2N6468	-120			
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-1.2	V
V _{BE}	Base-emitter on voltage	I _C =-1.5A; V _{CE} =-4V			-1.5	V
I _{CBO}	Collector cut-off current	2N6467			-10	μA
		2N6468				
I _{CEO}	Collector cut-off current	2N6467			-100	μA
		2N6468				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-1.5A; V _{CE} =-4V	15		150	
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V	5			MHz

PACKAGE OUTLINE

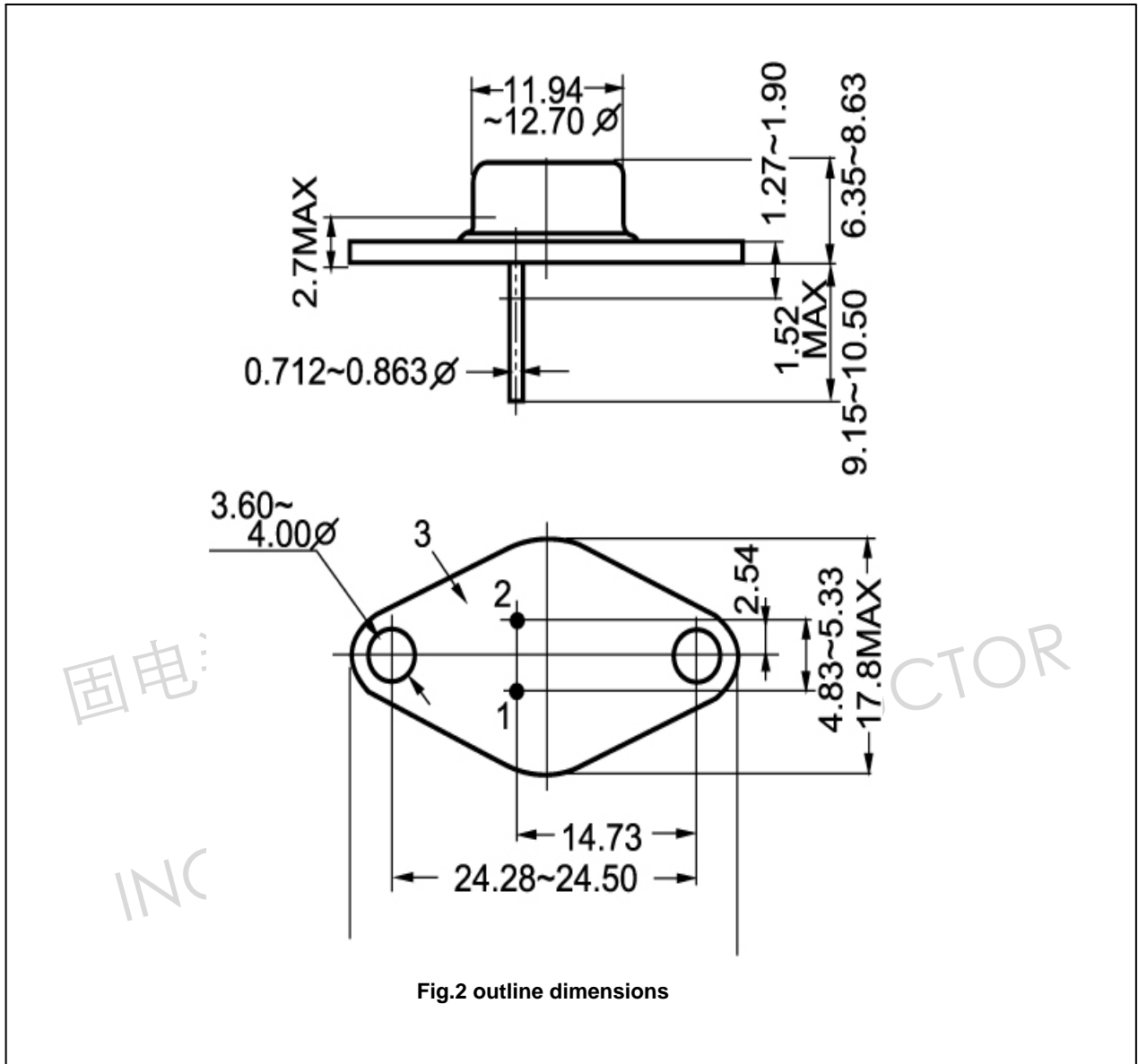


Fig.2 outline dimensions